

Amendment Under 37 C.F.R. §1.111  
Serial No. 10/816,958  
Attorney Docket No. 042323

**AMENDMENTS TO THE SPECIFICATION:**

Please amend the specification as follows:

**Amend the paragraph beginning on page 10, line 21 continuing on page 11, as follows:**

As described above, it is possible that nitrogen is adsorbed onto the surface of the interconnection layer of Cu as the main material by nitrogen-two-fluid processing, and the rate of generating the conduction defect of the interconnection layer is controlled low by the following mechanism even in high temperature environments. That is, when the diffusion preventing film for preventing the diffusion of Cu is formed with nitrogen adsorbed onto the surface of the interconnection layer of Cu as the main material, the presence of the nitrogen makes it difficult the migration of the Cu atoms in the interconnection layer in high temperature environments. It is considered that resultantly, the ~~generation~~ generation of voids in the interconnection layer is suppressed, the rate of generating the conduction defects of the interconnection layer is suppressed low, and the stress-migration resistance of the interconnection layer is increased.